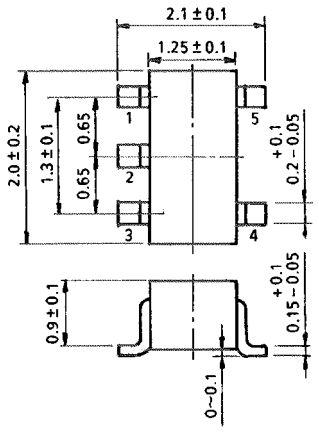
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

S S M 5 N 0 5 F U

High Speed Switching Applications

- Small package
- Low on resistance : R_{on} = 0.8 Ω (max) (@V_{GS} = 4 V)
  : R_{on} = 1.2 Ω (max) (@V_{GS} = 2.5 V)
- Low gate threshold voltage

Unit in mm



1. GATE 1
2. SOURCE
3. GATE 2
4. DRAIN 2
5. DRAIN 1

USV	
JEDEC	—
EIAJ	—
TOSHIBA	2-2L1B

Weight : 6.2 mg

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

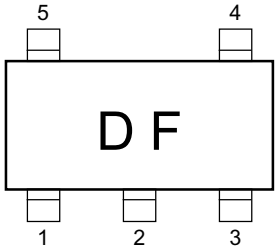
Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	20	V
Gate-Source voltage		V_{GSS}	±12	V
Drain current	DC	I_D	400	mA
	Pulse	I_{DP}	800	
Drain power dissipation (Ta = 25°C)		P_D (Note1)	300	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note1: Total rating, mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 0.32 mm^2 × 5)

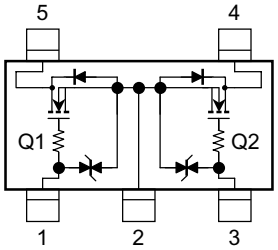
Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Marking



Equivalent Circuit (top view)



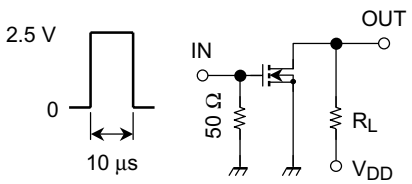
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±12 V, V_{DS} = 0	—	—	±1	μA
Drain-Source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 1 mA, V_{GS} = 0	20	—	—	V
Drain cut-off current		I_{DSS}	V_{DS} = 20 V, V_{GS} = 0	—	—	1	μA
Gate threshold voltage		V_{th}	V_{DS} = 3 V, I_D = 0.1 mA	0.6	—	1.1	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 200 mA (Note2)	350	—	—	mS
Drain-Source ON resistance		$R_{DS\ (ON)}$	I_D = 200 mA, V_{GS} = 4 V (Note2)	—	0.6	0.8	Ω
			I_D = 200 mA, V_{GS} = 2.5 V (Note2)	—	0.85	1.2	
Input capacitance		C_{iss}	V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz	—	22	—	pF
Reverse transfer capacitance		C_{rss}		—	9	—	pF
Output capacitance		C_{oss}		—	21	—	pF
Switching time	Turn-on time	t_{on}	V_{DD} = 3 V, I_D = 100 mA,	—	60	—	ns
	Turn-off time	t_{off}	V_{GS} = 0~2.5 V	—	70	—	

Note2: Pulse test

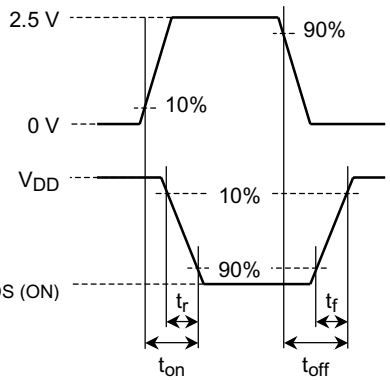
Switching Time Test Circuit

(a) Test circuit



V_{DD} = 3 V
Duty ≦ 1%
V_{IN}: t_r, t_f < 5 ns
(Z_{out} = 50 Ω)
Common Source
Ta = 25°C

(b) V_{IN}



(c) V_{OUT}

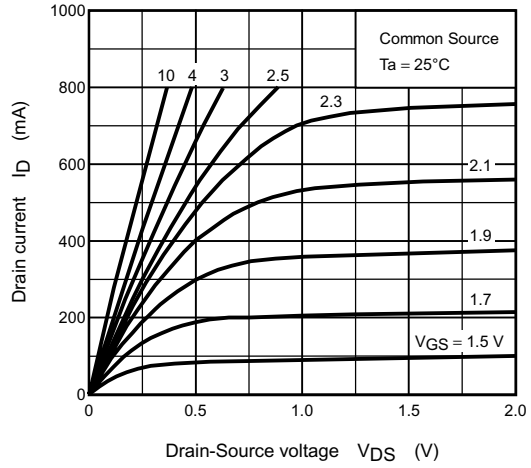
Precaution

V_{th} can be expressed as voltage between gate and source when low operating current value is I_D = 100 μA for this product. For normal switching operation, $V_{GS\ (on)}$ requires higher voltage than V_{th} and $V_{GS\ (off)}$ requires lower voltage than V_{th}. (Relationship can be established as follows: $V_{GS\ (off)} < V_{th} < V_{GS\ (on)}$)

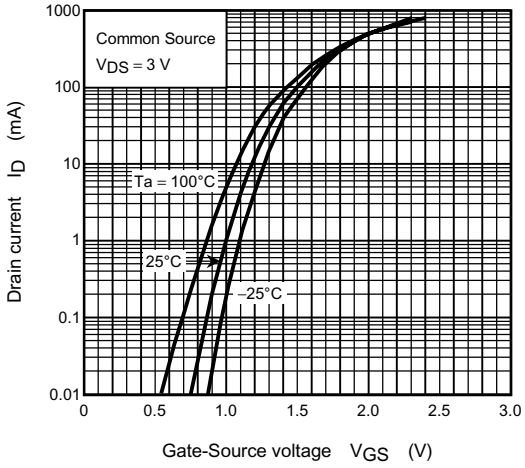
Please take this into consideration for using the device. V_{GS} recommended voltage of 2.5 V or higher to turn on this product.

(Q1, Q2 common)

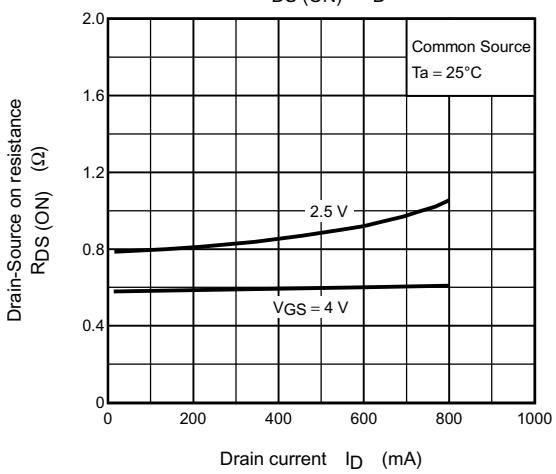
$I_D - V_{DS}$



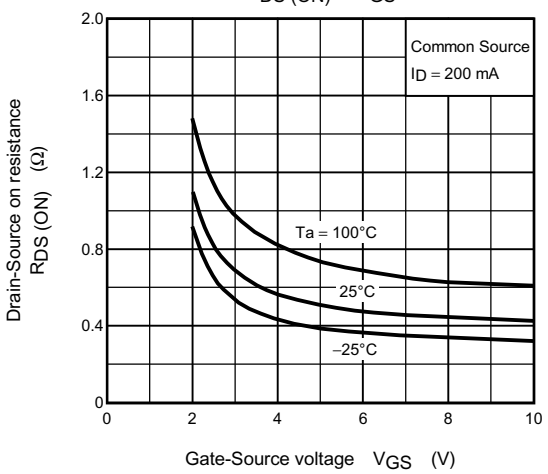
$I_D - V_{GS}$



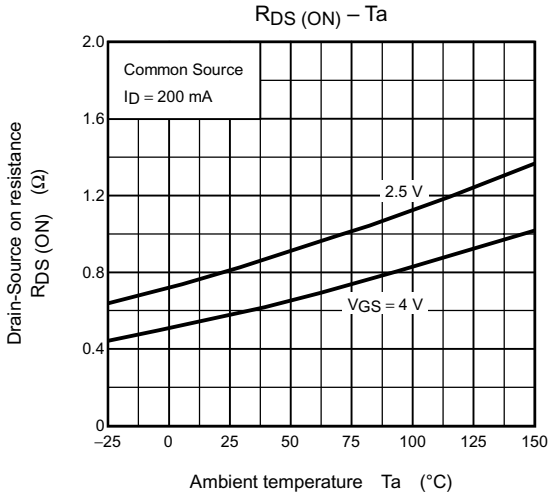
$R_{DS\ (ON)} - I_D$



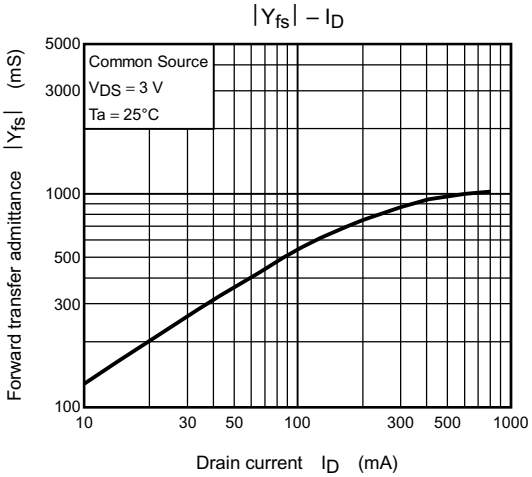
$R_{DS\ (ON)} - V_{GS}$



$R_{DS\ (ON)} - Ta$

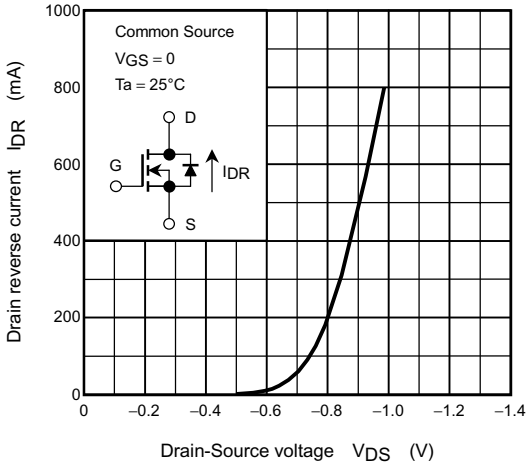


$|Y_{fs}| - I_D$

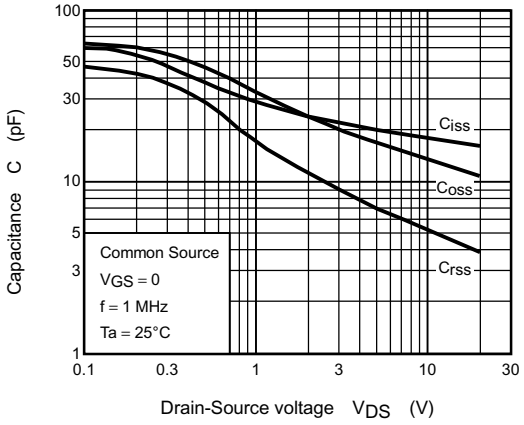


(Q1, Q2 common)

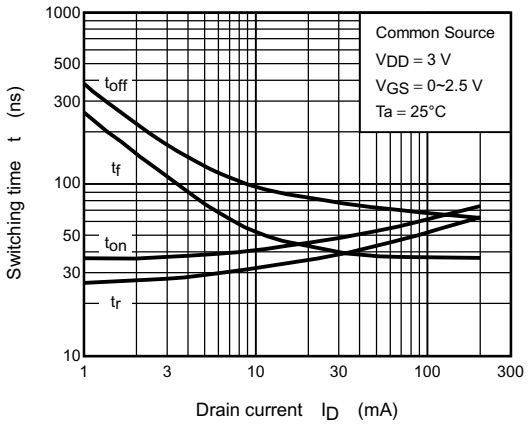
$I_{DR} - V_{DS}$



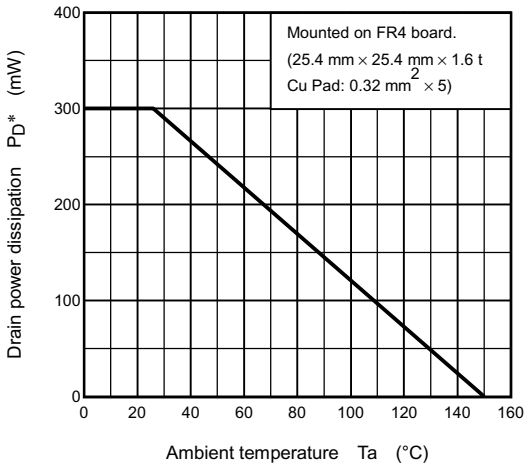
$C - V_{DS}$



$t - I_D$



$P_D^* - Ta$



*: Total rating